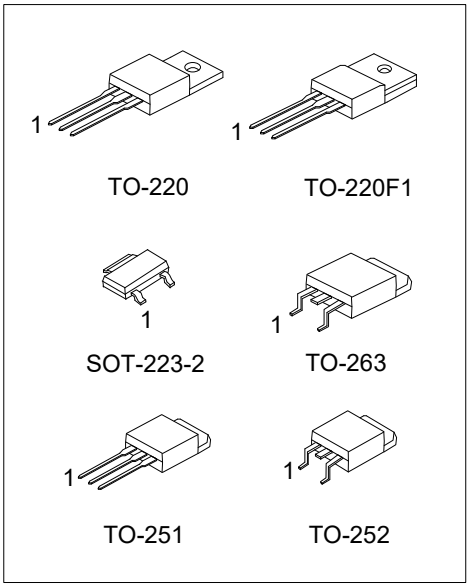
3NM80-Q **Preliminary** ***Power MOSFET***

3.0A, 800V N-CHANNEL SUPER-JUNCTION MOSFET



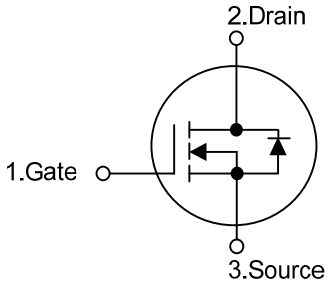
■ DESCRIPTION

The **UTC 3NM80-Q** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 3.0\ \Omega$ @ V_{GS}=10V, I_D=1.5A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

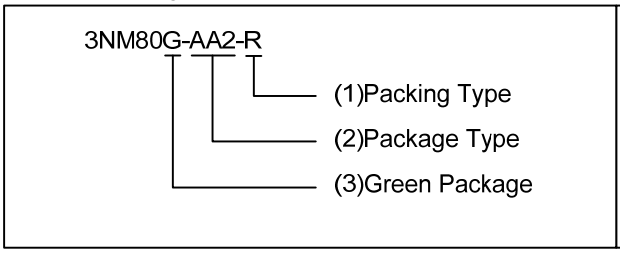
■ SYMBOL



■ ORDERING INFORMATION

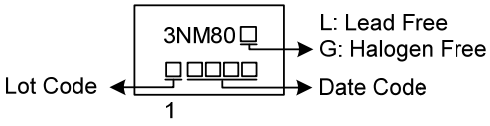
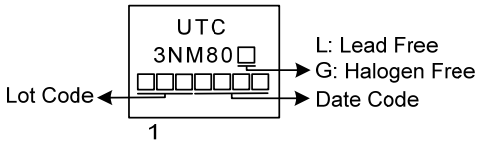
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3NM80L-AA2-R	3NM80G-AA2-R	SOT-223-2	G	D	S	Tape Reel
3NM80L-TA3-T	3NM80G-TA3-T	TO-220	G	D	S	Tube
3NM80L-TF1-T	3NM80G-TF1-T	TO-220F1	G	D	S	Tube
3NM80L-TM3-T	3NM80G-TM3-T	TO-251	G	D	S	Tube
3NM80L-TN3-R	3NM80G-TN3-R	TO-252	G	D	S	Tape Reel
3NM80L-T2Q-T	3NM80G-T2Q-T	TO-262	G	D	S	Tube
3NM80L-TQ2-R	3NM80G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) R: Tape Reel, T: Tube
(2) AA2: SOT-223-2, TA3: TO-220, TF1: TO-220F1
TM3: TO-251, TN3: TO-252, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

SOT-223-2	TO-220 / TO-220F1 TO-251 / TO-252 / TO-263
	

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	3	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	6	A
Single Pulsed Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	72	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.7	V/ns
Power Dissipation	SOT-223-2	P_D	1.8	W
	TO-220/TO-263		27	W
	TO-220F1		15	W
	TO-251/TO-252		16	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 100mH, I_{AS} = 1.2A, V_{DD} = 90V, R_G = 25Ω, Starting T_J = 25°C.
4. I_{SD} ≤ 3.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223-2	θ_{JA}	150	°C/W
	TO-220/TO-220F1 TO-263		62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	SOT-223-2	θ_{JC}	69.4	°C/W
	TO-220/TO-263		4.63	°C/W
	TO-220F1		8.33	°C/W
	TO-251/TO-252		7.8 (Note)	°C/W

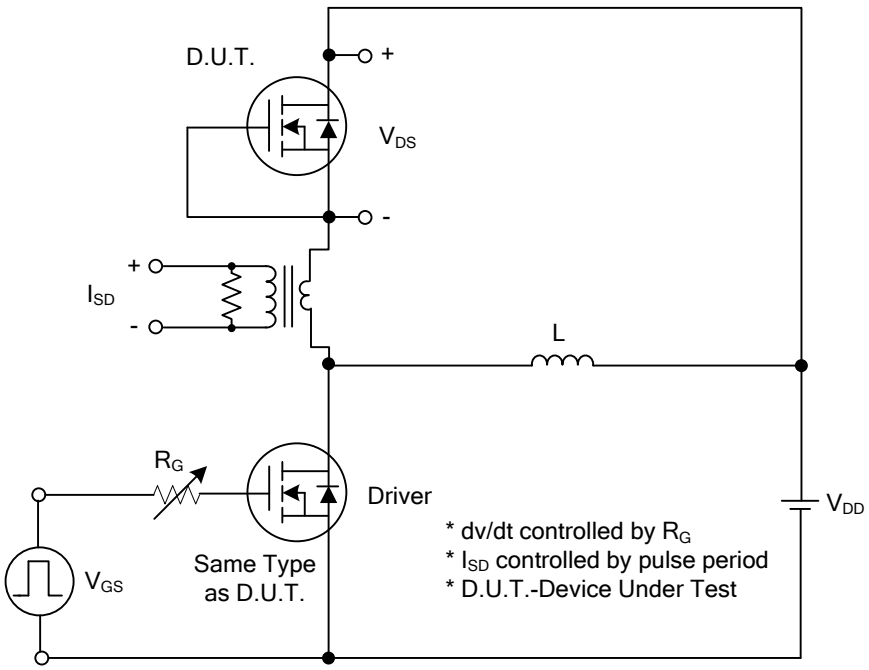
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

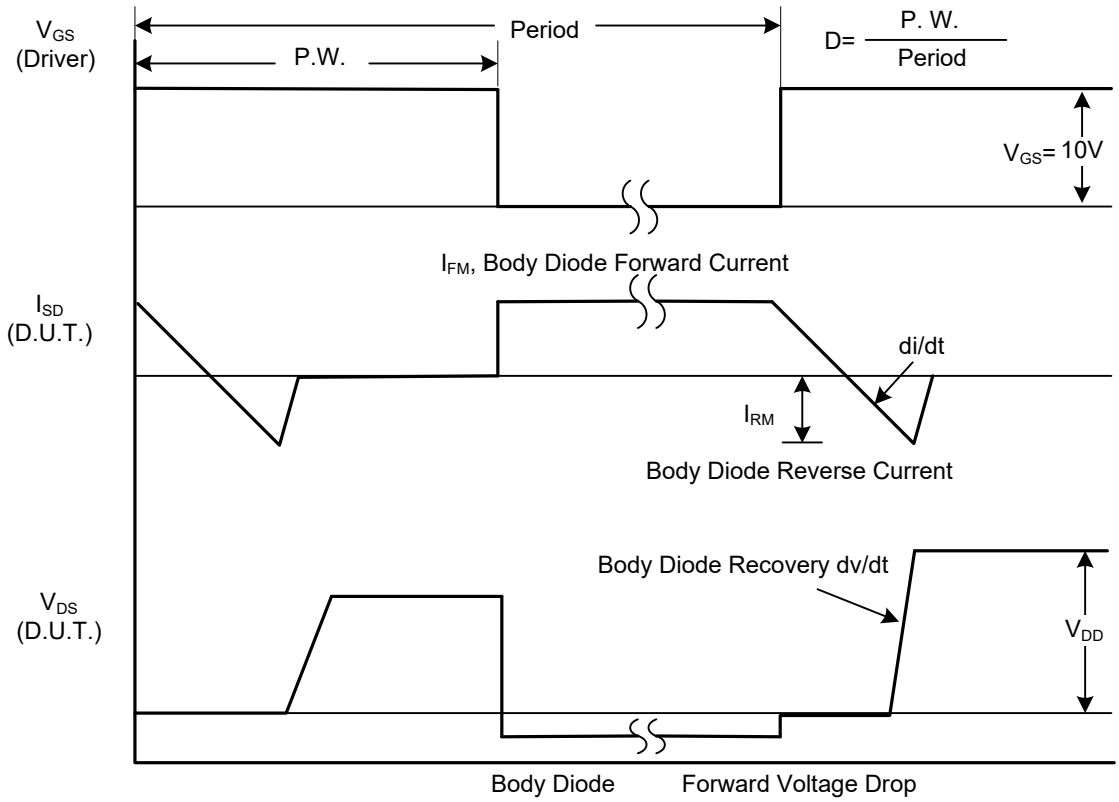
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	800			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=800V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=1.5A			3.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=50V, f=1.0MHz		200		pF
Output Capacitance		C_{OSS}			29		pF
Reverse Transfer Capacitance		C_{RSS}			2.7		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=640V, V_{GS}=10V, I_D=3.0A (Note 1, 2)		16		nC
Gate to Source Charge		Q_{GS}			5		nC
Gate to Drain Charge		Q_{GD}			4		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=100V, V_{GS}=10V, I_D=3.0A, R_G=25Ω (Note 1, 2)		4.8		nS
Rise Time		t_R			16		nS
Turn-OFF Delay Time		$t_{D(OFF)}$			30		nS
Fall-Time		t_F			28		nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				3	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				6	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=3.0A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S=3.0A, V_{GS}=0V, dI_F/dt=100A/μs		270		nS
Body Diode Reverse Recovery Charge		Q_{rr}			1.5		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

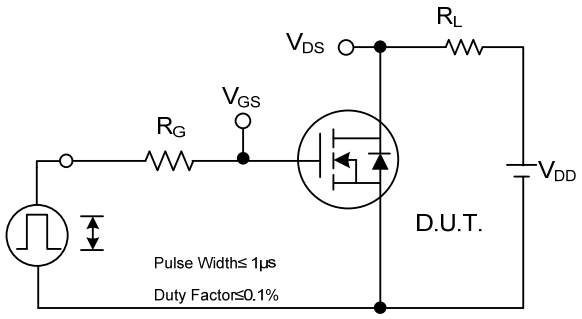


Peak Diode Recovery dv/dt Test Circuit

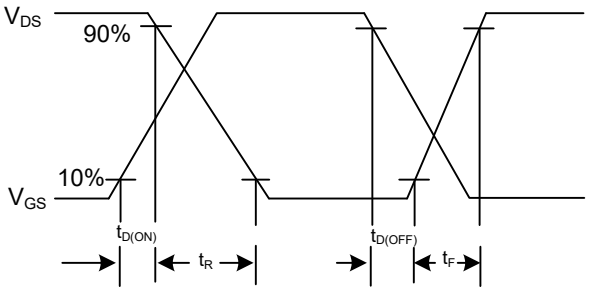


Peak Diode Recovery dv/dt Waveforms

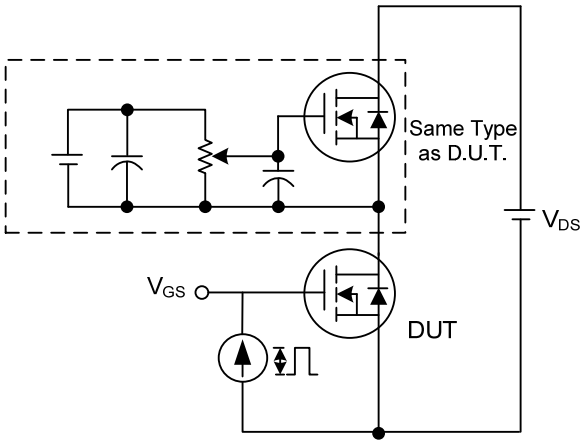
■ TEST CIRCUITS AND WAVEFORMS



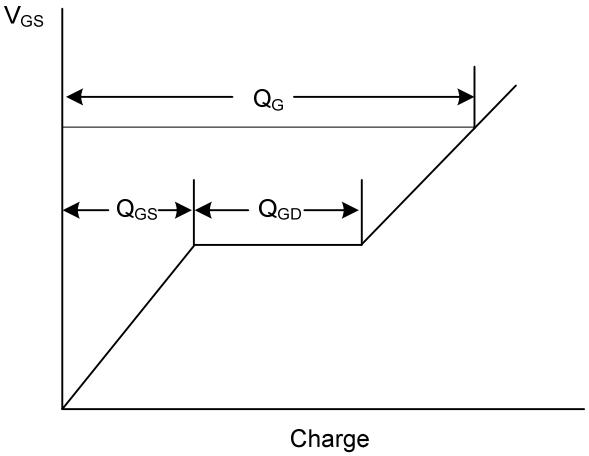
Switching Test Circuit



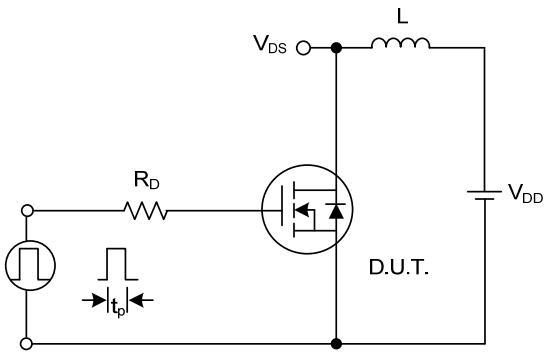
Switching Waveforms



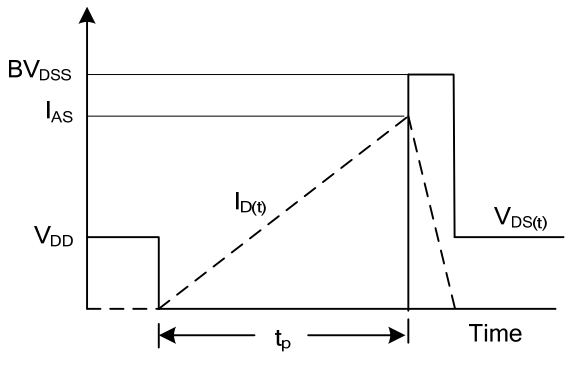
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms